Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
Tech ID: 32270 / UC Case 2021-551-0

BACKGROUND
P-type gallium nitride (p-GaN) is difficult to contact electrically and has a low hole concentration and mobility in conventional commercial III-nitride LEDs. This means that p-GaN cannot be used as a current spreading layer and that traditional p-contacts will add significant voltage to devices. Despite these inherent problems, all commercial light emitting devices utilize traditional p-contacts and materials other than p-GaN for current spreading, which typically involves a high barrier for tunneling. Unfortunately, current approaches to reduce the tunneling barrier are associated with losses, either in terms of voltage or resistance increases, or optical losses in the final device performance. These penalties exist even in smaller LED devices such as mini-LEDs and micro-LEDs.

DESCRIPTION
Researchers at the University of California, Santa Barbara have fabricated low forward voltage micro-LEDs with an epitaxial tunnel junction comprised of p+GaN, an In$_x$Al$_{1-x}$Ga$_2$N insertion layer, and n+GaN layers grown using metalorganic chemical vapor deposition (MOCVD). The In$_x$Al$_{1-x}$Ga$_2$N insertion layer offers a smaller energy bandgap than the GaN layers, which works to reduce the depletion width of the tunnel junctions and increase the tunnel probability. Tunnel junction micro-LEDs with an n-type and p-type In$_x$Al$_{1-x}$Ga$_2$N insertion layer demonstrated a very stable low forward voltage at 20A cm$^{-2}$. Therefore, fabrication of micro-LEDs with low forward voltage is achieved, increasing the potential for next-generation display applications.

ADVANTAGES
- Low forward voltage
- Reduced tunnel junction depletion width
- Increased tunnel probability

APPLICATIONS
- Micro-LEDs

PATENT STATUS
Patent Pending

RELATED MATERIALS
- Fully transparent metal-organic chemical vapor deposition-grown cascaded InGaN micro-light-emitting diodes with independent junction control - 06/25/2021

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS
- Method for Improved Surface of (Ga,Al,In,B)N Films on Nonpolar or Semipolar Substrates
- Enhanced Optical Polarization of Nitride LEDs by Increased Indium Incorporation
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- III-Nitride-Based Devices Grown With Relaxed Active Region
- Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
Defect Reduction in GaN films using in-situ SiNx Nanomask
Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
Highly Efficient Blue-Violet III-Nitride Semipolar Laser Diodes
Hybrid Growth Method for Improved III-Nitride Tunnel Junction Devices
Low Temperature Deposition of Magnesium Doped Nitride Films
Transparent Mirrorless (TML) LEDs
Improved GaN Substrates Prepared with Ammonothermal Growth
Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
Size-Independent Forward Voltage Micro-LED with an Epitaxial Junction
Method for Enhancing Growth of Semipolar Nitride Devices
III-Nitride Tunnel Junction with Modified Interface
Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
Nonpolar III-Nitride LEDs With Long Wavelength Emission
Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
Increased Light Extraction with Multistep Deposition of ZnO on GaN
Method for Manufacturing Improved III-Nitride LEDs and Laser Diodes: Monolithic Integration of Optically Pumped and Electrically Injected III-Nitride LEDs
Selective-Area Mesoporous Semiconductors And Devices For Optoelectronic And Photonic Applications
High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
Method for Growing High-Quality Group III-Nitride Crystals
Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
Oxyfluoride Phosphors for Use in White Light LEDs
Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
\( (In,Ga,Al)N \) Optoelectronic Devices with Thicker Active Layers for Improved Performance
Thermally Stable, Laser-Driven White Lighting Device
MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
Highly Compact, High-Index Dielectric Nanostructures for Deep-Ultraviolet Devices
Reduction in Leakage Current and Increase in Efficiency of III-Nitride MicroLEDs
Methods for Fabricating III-Nitride Tunnel Junction Devices
Low-Droop LED Structure on GaN Semi-polar Substrates
Contact Architectures for Tunnel Junction Devices
Nonpolar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
Photoelectrochemical Etching Of P-Type Semiconductor Heterostructures
Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
Growth of Semipolar III-V Nitride Films with Lower Defect Density
III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
Improved Manufacturing of Solid State Lasers via Patterned of Photonic Crystals
High Efficiency III-Nitride Devices with Smooth Relaxed InGaN Buffer and Strain Compliant Template
Multifaceted III-Nitride Surface-Emitting Laser
Tunable White Light Based on Polarization-Sensitive LEDs
Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
Growth of High-Performance M-plane GaN Optical Devices
Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
Improved Anisotropic Strain Control in Semipolar Nitride Devices
High Light Extraction Efficiency III-Nitride LED
III-V Nitride Device Structures on Patterned Substrates
Method for Increasing GaN Substrate Area in Nitride Devices
Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
GaN-Based Thermoelectric Device for Micro-Power Generation
Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
LED Device Structures with Minimized Light Re-Absorption
Growth of Planar Semi-Polar Gallium Nitride
Nonpolar (Al, B, In, Ga)N Quantum Well Design
UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
Defect Reduction of Non-Polar and Semi-Polar III-Nitrides

III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture

Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD